

Silicon PNP Power Transistors

2SB744 2SB744A

DESCRIPTION

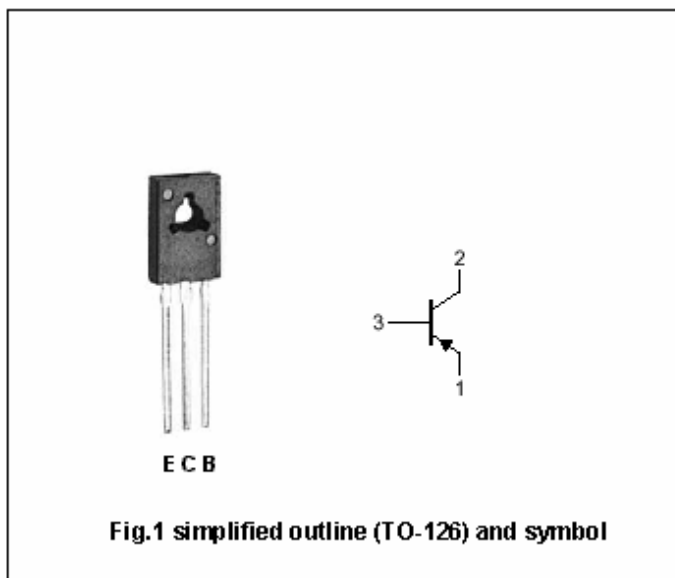
- With TO-126 package
- Complement to type 2SD794/794A
- Excellent h_{FE} linearity

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	2SB744	Open base	-45	V
		2SB744A		-60	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current (DC)			-3	A
I_{CM}	Collector current-Peak			-5	A
I_B	Base current			-0.6	A
P_C	Collector power dissipation		$T_a=25$	1	W
			$T_c=25$	10	
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB744	$I_C=-10mA; I_B=0$	-45			V
		2SB744A		-60			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=-1.5A; I_B=-0.15A$		-0.5	-2.0	V
V_{BEsat}	Base-emitter saturation voltage		$I_C=-1.5A; I_B=-0.15A$		-0.8	-2.0	V
I_{CBO}	Collector cut-off current		$V_{CB}=-45V; I_E=0$			-1	μA
I_{EBO}	Emitter cut-off current		$V_{EB}=-3V; I_C=0$			-1	μA
h_{FE-1}	DC current gain		$I_C=-20mA; V_{CE}=-5V$	30	120		
h_{FE-2}	DC current gain		$I_C=-0.5A; V_{CE}=-5V$	60	100	320	
f_T	Transition frequency		$I_C=-0.1A; V_{CE}=-5V$		45		MHz
C_{OB}	Collector output capacitance		$f=1MHz; V_{CB}=-10V; I_E=0$		60		pF

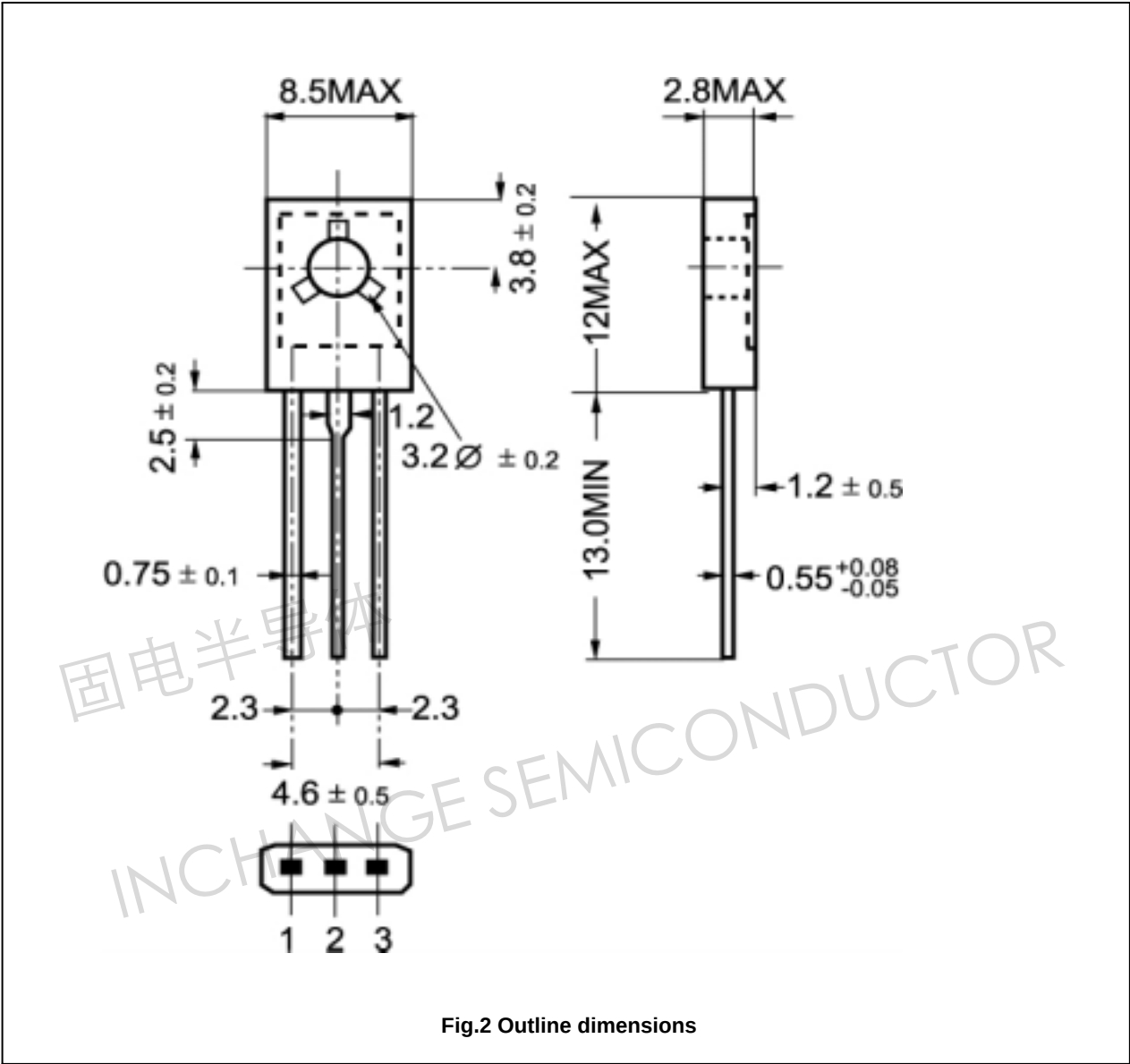
◆ h_{FE-2} Classifications

R	O	Y
60-120	100-200	160-320

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PACKAGE OUTLINE



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